

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	@pn="4016593"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/04/12 12:19
L2	7	("4016593").URPN.	USPAT	OR	ON	2005/04/12 14:24
S1	3	(semiconductor adj wafer) and (chip adj forming adj section)	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 11:30
S2	1651	(semiconductor adj wafer) and (plurality multiple) adj chip	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 11:30
S3	252	S2 and electrode and @ad<="20000627"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 11:30
S4	45	S3 and (hole near12 electrode)	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 14:49
S5	3964	hole adj electrode	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 11:43
S6	1000	through adj hole adj electrode	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 11:43
S7	559	S6 and @ad<="20000627"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 12:05
S8	17	S7 and semiconductor adj wafer	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 11:44

S9	16	S3 and (through adj hole near12 electrode)	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 12:04
S10	16	S9 and @ad<="20000627"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 13:18
S11	341	semiconductor and "second through hole" and @ad<="20000627"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 13:32
S12	72	S11 and ((through adj hole) near5 electrode)	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 13:35
S13	2	"4696885".pn.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 13:38
S14	2	"5918113".pn.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 13:45
S15	2	"6114192".pn.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 13:47
S16	2	"6333564".pn.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 13:52
S17	2	"6358762".pn.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 13:53
S18	2	"6358836".pn.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 14:06

S19	19	"6388313"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 14:06
S20	2	"6388313".pn.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 14:11
S25	795	third adj through adj hole	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 15:01
S26	17	S25 and "438"/\$.ccls. and @ad<="20000627"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 16:33
S27	121	((through adj hole) near3 electrode) and (second adj through adj hole)and @ad<="20000627"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 16:35
S28	31	S27 and (third adj through adj hole)	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/23 16:35
S29	788	438/629.ccls.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 08:43
S30	379	438/629.ccls. and @ad<="20000627"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 09:02
S31	106	(etch near3 (hole via) near3 electrode) and @ad<="20000627"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 09:40
S32	1053	438/637.ccls. and @ad<="20000627"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 09:37

S33	328	438/638.ccls. and @ad<="20000627"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 10:51
S34	362	438/639.ccls. and @ad<="20000627"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 14:27
S35	128	438/667.ccls. and @ad<="20000627"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 14:32
S36	998	257/774.ccls. and @ad<="20000627"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 14:32
S37	1659	(semiconductor adj wafer) and (plurality multiple) adj chip	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 14:49
S38	252	S37 and electrode and @ad<="20000627"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 15:28
S39	26	S38 and ((hole via) near2 electrode)	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 14:50
S40	111	S37 and ((hole via) near2 electrode)	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 14:54
S41	30	S40 and (second near2 (hole via))	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 14:54
S42	26	S40 and @ad<="20000627"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 15:35

S43	4	S41 and @ad<="20000627"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 15:35
S44	21	((hole via) adj electrode) and dielectric adj electrode	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 15:52
S46	13	S44 and @ad<="20000627"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 15:51
S47	3	((hole via) adj electrode) and dielectric adj over adj electrode	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 15:54
S48	6	((hole via) near2 electrode) and dielectric adj over adj electrode	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/25 16:49
S49	4	S48 and @ad<="20000627"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 15:56
S51	2	"6252266".pn.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:30
S52	35	hoshi.in. and mitsubishi.as.	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/24 16:33
S53	287	hoshi.in. and mitsubishi.as.	JPO	OR	ON	2005/03/24 16:33
S56	4	S53 and transistor	JPO	OR	ON	2005/03/25 08:19
S58	1	JP409153516A	JPO	OR	ON	2005/03/25 14:11
S60	2	"5918133".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/25 14:12

S61	6	higoshi.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/25 14:13
S62	2649	higashi.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/25 14:13
S63	23	"5918133"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/25 14:16
S64	2	"6682948".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/25 14:16
S65	2	"5918113".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/25 14:22
S66	2	"6304484".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/25 14:24
S67	2	"5753952".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/25 14:35
S68	292	hole near6 etch near6 electrode and @ad<="20000627"	US-PGPUB; USPAT; USOCR; DERWENT; IBM_TDB	OR	ON	2005/03/25 16:50
S69	298	hole near6 etch near6 electrode and @ad<="20000627"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/25 16:51

S70	93	hole near3 etch near3 electrode and @ad<="20000627"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/25 16:52
S71	3	etch adj through adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/25 16:54
S72	0	etch adj hole adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/25 16:54
S73	53	etch near2 hole near2 electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/25 16:59
S74	32	etch near2 hole near2 electrode and @ad<="20000627"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 16:10
S75	56	etch near2 hole near3 electrode and @ad<="20000627"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/28 16:10